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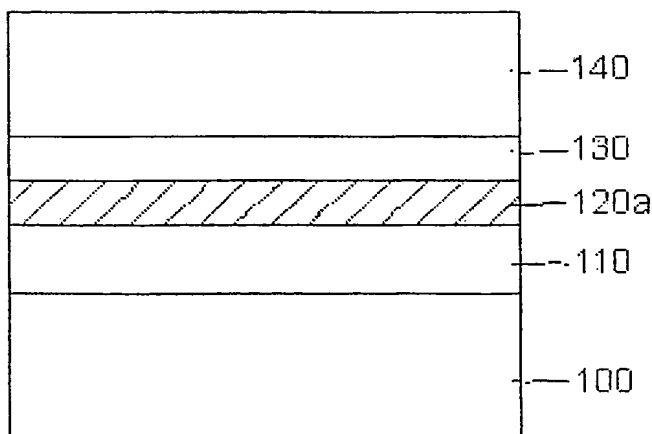
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(54) Title: GROWTH METHOD OF NITRIDE SEMICONDUCTOR EPITAXIAL LAYERS



(57) Abstract: The present invention relates to a method for growing a nitride semiconductor epitaxial layer, which comprises the steps of growing a second nitride semiconductor epitaxial layer on a first nitride semiconductor epitaxial layer at a first temperature, growing a third nitride semiconductor epitaxial layer on the second nitride semiconductor epitaxial layer at a second temperature, and releasing nitrogen from the second nitride semiconductor epitaxial layer by increasing a temperature to a third temperature higher than the second temperature, thereby, it is possible to lower the defect density of epitaxial layers and reduce warpage of a substrate.

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